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Mill-Jer Wang; Jiang, R.-L.; Hsia, J.-W.; Chih-Hu Wang; Chen, J.I
Test Symposium, 2001. Proceedings. 10th Asian
19-21 Nov. 2001 Page(s):151 - 156
Digital Object Identifier 10.1109/ATS.2001.990274

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2. **Power supply current detectability of SRAM defects**

Jian Liu; Makki, R.;
Test Symposium, 1995., Proceedings of the Fourth Asian
23-24 Nov. 1995 Page(s):367 - 373
Digital Object Identifier 10.1109/ATS.1995.485362

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Lu Ling; Xu Jia; Que Dashun; Nie Mingxin; Huang Hongxing;
Electromagnetic Compatibility, 2002 3rd International Symposium
21-24 May 2002 Page(s):218 - 221

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4. **Melt filaments in n⁺pn⁺ lateral bipolar ESD protection device**

Clark, N.K.; Parat, K.; Maloney, T.J.; Yudong Kim;
Electrical Overstress/Electrostatic Discharge Symposium Proceedings
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Digital Object Identifier 10.1109/EOSESD.1995.478297

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Shibata, N.; Morimura, H.; Watanabe, M.;

Solid-State Circuits, IEEE Journal of

Volume 34, Issue 6, June 1999 Page(s):866 - 877

Digital Object Identifier 10.1109/4.766821

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2. Reliability degradation of high density DRAM cell transistor j

leakage current induced by band-to-defect tunneling under th

bias-temperature stress

Young Pil Kim; Young Wook Park; Joo Tae Moon; Kim, S.U.;

Reliability Physics Symposium, 2001. Proceedings. 39th Annual. International

30 April-3 May 2001 Page(s):1 - 6

Digital Object Identifier 10.1109/RELPHY.2001.922872

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3. Gate-Length Biasing for Runtime Leakage

Gupta Puneet ; Kahng Andrew ;

IEEE Transactions on Computer-Aided Design of Integrated Circ

Systems : Accepted for future publication

Volume PP, Issue 99, 2005 Page(s):1 - 1

Digital Object Identifier 10.1109/TCAD.2005.857313

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4. Study of stress-induced leakage current and charge loss of r

memory cell with 70 /spl Aring/ tunnel oxide using floating-g

technique

Bin Wang; Chih-Hsin Wang; Yanjun Ma; Diorio, C.; Humes, T.;

Integrated Reliability Workshop Final Report, 2004 IEEE Internati

18-21 Oct. 2004 Page(s):28 - 31

Digital Object Identifier 10.1109/IRWS.2004.1422732

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5. Wide-load-range resonant converter supplying the SAE J-171 vehicle inductive charging interface
Hayes, J.G.; Egan, M.G.; Murphy, J.M.D.; Schulz, S.E.; Hall, J.T.; Industry Applications, IEEE Transactions on Volume 35, Issue 4, July-Aug. 1999 Page(s):884 - 895 Digital Object Identifier 10.1109/28.777198
[AbstractPlus](#) | [References](#) | Full Text: [PDF\(328 KB\)](#) IEEE JNL
6. Experimental and theoretical investigation of nonvolatile memory retention
De Salvo, B.; Ghibaudo, G.; Pananakakis, G.; Reimbold, G.; Mon Guillaumot, B.; Candelier, P.; Electron Devices, IEEE Transactions on Volume 46, Issue 7, July 1999 Page(s):1518 - 1524 Digital Object Identifier 10.1109/16.772505
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